

ACJT105-6V 1A TRIAC

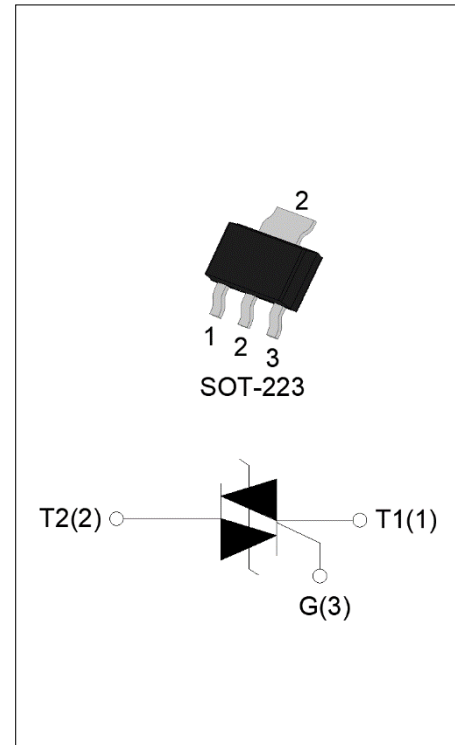
Rev.A.1.0

DESCRIPTION:

The ACJT105-6V triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT105-6V embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package SOT-223 is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III}$	5/5/5	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 90^\circ\text{C}$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	15	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		16.5	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1.25	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	50	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	5	W

Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	3.5	kV
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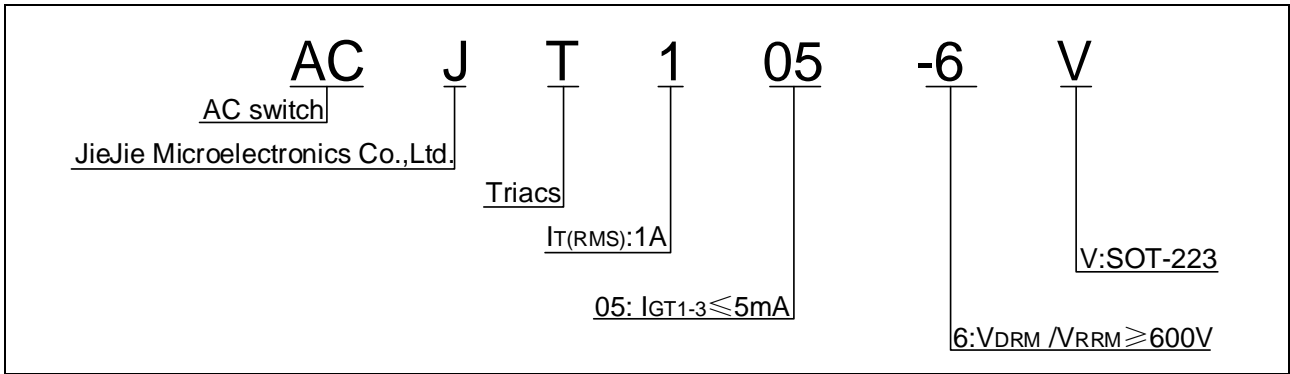
ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33$	I - II - III	MAX.	5	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	10	mA
		II		20	
I_H	$I_T=100\text{mA}$		MAX.	10	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	700	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10\text{V}/\mu\text{s}$, $T_j=125^\circ\text{C}$		MIN.	0.5	A/ms
t_{on}	$I_G=10\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	2	μs
t_{off}				20	
V_{CL}	$I_{CL}=0.1\text{mA}$ $t_p=1\text{ms}$		MIN.	700	V

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.8	V
R_D	Dynamic resistance	$T_j=25^\circ\text{C}$		

ORDERING INFORMATION



MARKING

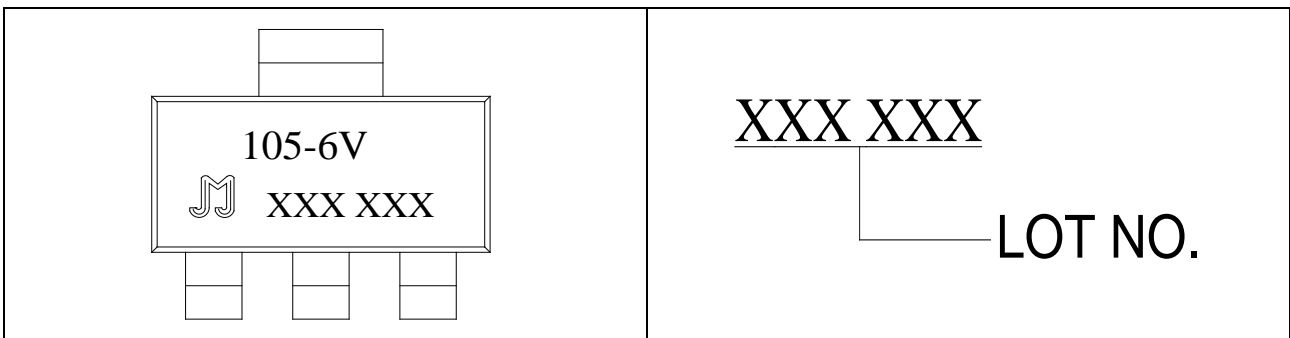


FIG.1 Maximum power dissipation versus RMS on-state current

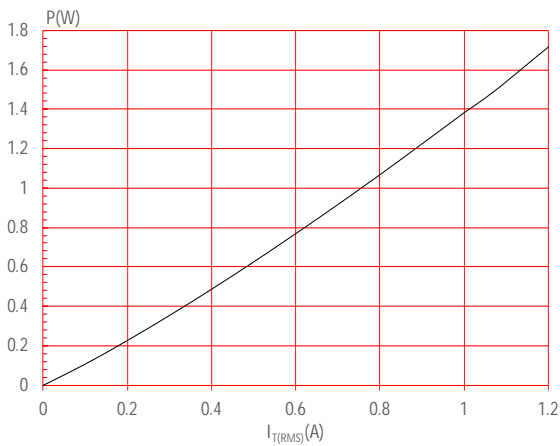


FIG.2: RMS on-state current versus case temperature

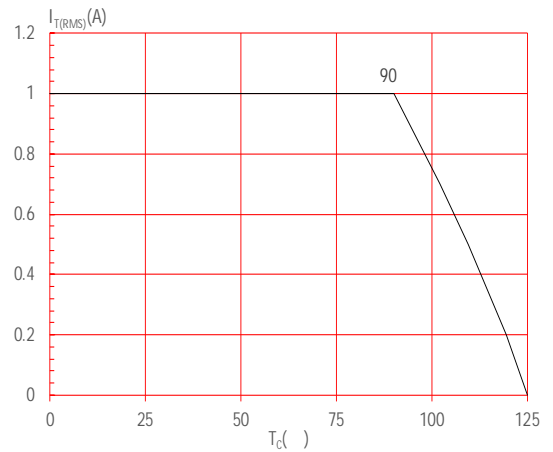


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

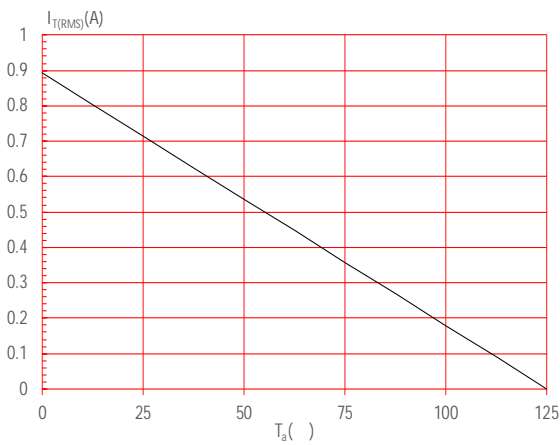


FIG.4: Surge peak on-state current versus number of cycles

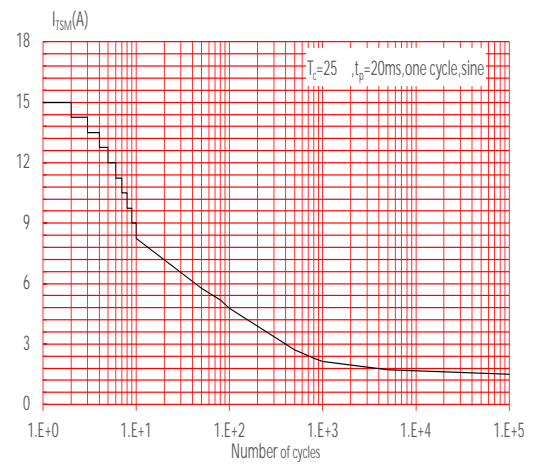


FIG.5: On-state characteristics

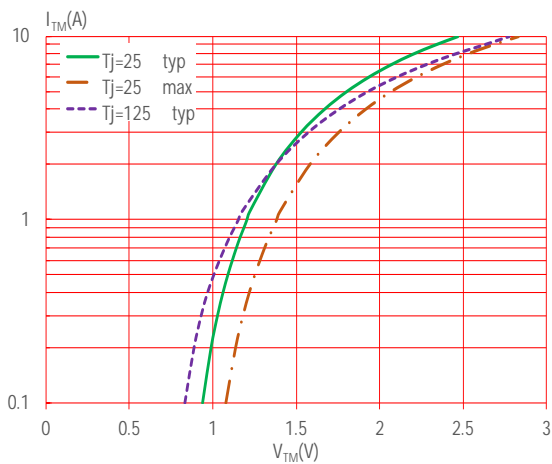


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

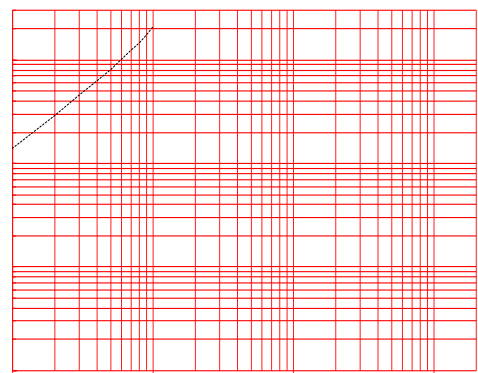


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

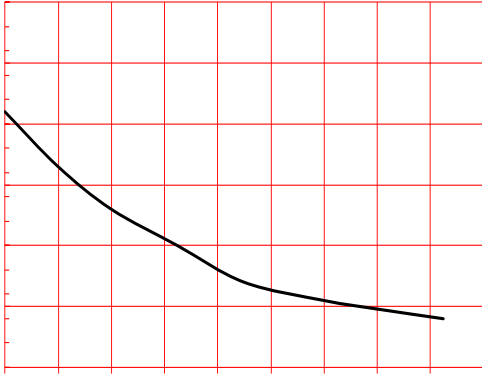


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

ORDERING INFORMATION

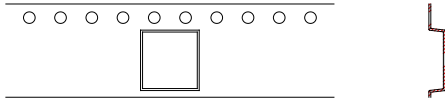
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT105-6V	600	5	SOT-223	4,000	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA


DELIVERY MODE



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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